XP0NG8A

Silicon PNP epitaxial planar type (Tr) Silicon epitaxial planar type (SWD)

For digital circuits

Features

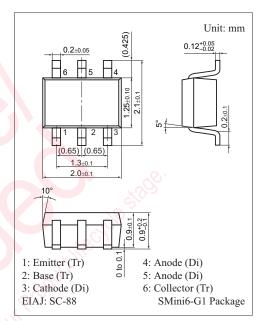
- Two elements incorporated into one package (Tr + SWD)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- SMini type package allowing easy automatic insertion through tape packing and magazine packing

Basic Part Number

• UNR211L + MA3X152E

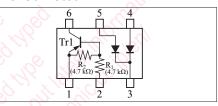
Absolute Maximum Ratings $T_a = 25^{\circ}C$

lector-base voltage litter open)	V _{CBO}	-50	V
lector-emitter voltage se open)	V _{CEO}	-50	v .
lector current	I _C	-100	mA
ward current	I _F	100	mA
k forward current	I _{FM}	225	mA
	I _{FSM}	500	mA
erse voltage	VR	80	(V)
	V _{RM}	80	No.V
I power dissipation	P _T	150	mW
ction temperature	Tj	150	°C %
age temperature	T _{stg}	-55 to +150	°C
	se open) lector current ward current k forward current -repetitive peak forward e current * erse voltage kimum peak reverse age al power dissipation ction temperature age temperature	se open) V_{CEO} lector current I_C ward current I_F k forward current I_{FM} -repetitive peak forward te current * I_{FSM} erse voltage V_R kimum peak reverse age V_{RM} al power dissipation P_T ction temperature T_j	se open) V_{CEO} -50 lector current I_C -100 ward current I_F 100 k forward current I_{FM} 225 -repetitive peak forward ge current* I_{FSM} 500 erse voltage V_R 80 kimum peak reverse age V_{RM} 80 al power dissipation P_T 150 ction temperature T_j 150



Marking Symbol: 4D

Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, \ I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			-2.0	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	20			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V _{OH}	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -0.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V _{OL}	$V_{\rm CC} = -5 \text{ V}, V_{\rm B} = -2.5 \text{ V}, R_{\rm L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	R ₁		-30%	4.7	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.8	1.0	1.2	
Transition frequency	f _T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$	E S	80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• SWD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V _F	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage	V _R	$I_R = 100 \ \mu A$	80		30	V
Reverse current	I _R	$V_R = 75 V$	8		0.1	μΑ
Terminal capacitance	Ct	$V_{R} = 0 V, f = 1 MHz$	Ser l	Ô.	2.0	pF
Reverse recovery time	t _{rr}	$I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ω, $I_{rr} = 0.1$ I_R		Still .	3.0	ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

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